Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	test$3 near10 bridg$3 near10 (DRAM (random near3 access near3 memory))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 16:10
L2	3	test$3 near10 bridg$3 near10 (DRAM (random near3 access near3 memory))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:10
L3	9	(test$3 detect$3) near10 bridg$3 near10 (DRAM (random near3 access near3 memory))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 16:13
L4	5	(test$3 detect$3) near10 bridg$3 near10 (DRAM (random near3 access near3 memory))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:13
S1	25391	test$3 near10 (IC (integrated near3 circuit) DRAM (random near3 access near3 memory))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:48
S2	3247	S1 and ((bit near3 line) bit-line bitline bit?line)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:49
S3	2084	S2 and ((word near3 line) word?line wordline word-line)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:15
S4	613	S3 and (activ$6 near10 ((bit near3 line) bit-line bitline bit?line))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:49
S5	96	S3 and (dummy near10 ((bit near3 line) bit-line bitline bit?line))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:16
S6	58	S4 and S5	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:20
S7	5	S6 and (contact near3 pad)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/08 15:27
S8	23596	test$3 near10 (IC (integrated near3 circuit) DRAM (random near3 access near3 memory))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:48
S9	285	S8 and ((bit near3 line) bit-line bitline bit?line)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:49
S10	20	S9 and (activ$6 near10 ((bit near3 line) bit-line bitline bit?line))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:49